Bekir Gurbulak

List of Publications by Year
in descending order

55	1,144	394421 19	414414 32
papers	citations	h-index	g-index

55	55	55	1356
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Analysis of temperature dependent current-voltage characteristics of Sn/p-GaTe/In Schottky diode. Optical Materials, 2022, 125, 112138.	3.6	7
2	Effect of voltages on Î³â˜Ray linear attenuation coefficients for some semiconductors. Radiation Physics and Chemistry, 2021, 179, 109208.	2.8	0
3	Effect of Temperature and Illumination on the Currentâ€“Voltage Characteristics of a Al/p-GaSe/In Diode. Journal of Electronic Materials, 2020, 49, 5698-5704.	2.2	4
4	Enhanced Electrocatalytic Activity in GaSe and InSe Nanosheets: The Role of Surface Oxides. Advanced Functional Materials, 2020, 30, 2005466.	14.9	35
5	Liquid Phase Exfoliated Indium Selenide Based Highly Sensitive Photodetectors. Advanced Functional Materials, 2020, 30, 1908427.	14.9	42
6	Silicon-doping influence on the crystalline, surface and optical features of cadmium oxide films deposited by sol-gel spin route. Optik, 2018, 165, 310-318.	2.9	11
7	Liquidâ€Phase Exfoliated Indiumâ€“Selenide Flakes and Their Application in Hydrogen Evolution Reaction. Small, 2018, 14, e1800749.	10.0	90
8	Electrical characterization of In/p-GaSe:Cd/Auâ€“Ge single crystal grown by Bridgman/Stockbarger method. AIP Conference Proceedings, 2017, , .	0.4	0
9	Indium selenide: an insight into electronic band structure and surface excitations. Scientific Reports, 2017, 7, 3445.	3.3	60
10	Growth and structural characterizations of GaSe and GaSe:Cd single crystals. AIP Conference Proceedings, 2017, , .	0.4	2
11	The Advent of Indium Selenide: Synthesis, Electronic Properties, Ambient Stability and Applications. Nanomaterials, 2017, 7, 372.	4.1	50
12	Growth of InSe:Mn semiconductor crystals by Bridgmanâ€“Stockbarger technique and analysis of electron irradiation effects on Sn/InSe:Mn Schottky diodes. Radiation Effects and Defects in Solids, 2016, 171, 528-543.	1.2	0
13	Lutentium incorporation influence on ZnO thin films coated via a solâ€“gel route: spin coating technique. Journal of Materials Science: Materials in Electronics, 2016, 27, 5089-5098.	2.2	2
14	The effect of Sn doping Urbach Tail and optical absorbtion measurements of InSe crystal. Journal of Physics: Conference Series, 2016, 707, 012027.	0.4	7
15	The influence of chemical reactivity of surface defects on ambient-stable InSe-based nanodevices. Nanoscale, 2016, 8, 8474-8479.	5.6	92
16	Electrical properties of Al/pâ€“Ge and Al/Methyl Green/pâ€“Ge diodes. Philosophical Magazine, 2015, 95, 1646-1655.	1.6	7
17	Currentâ€“Voltage and Capacitanceâ€“Conductanceâ€“Voltage Characteristics of Al/SiO2/p-Si and Al/Methyl Green (MG)/p-Si Structures. Metallurgical and Materials Transactions A: Physical Metallurgy and Materials Science, 2015, 46, 347-353.	2.2	10
18	The synthesis and characterization of solâ€“gel spin coated CdO thin films: As a function of solution molarity. Materials Letters, 2014, 126, 232-235.	2.6	34

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19	Fabrication and characterization of Al/<scp>C</scp>u₂<scp>Z</scp>n<scp>S</scp>n<scp>S</scp>₄/nâ€<scp>S</scp>i/<scp>A</scp>l heterojunction photodiodes. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 580-586.	1.8	31
20	Structural characterizations and optical properties of InSe and InSe:Ag semiconductors grown by Bridgman/Stockbarger technique. Physica E: Low-Dimensional Systems and Nanostructures, 2014, 64, 106-111.	2.7	39
21	An investigation of Zn/ZnO:Al/p-Si/Al heterojunction diode by solâ€“gel spin coating technique. Journal of Sol-Gel Science and Technology, 2014, 71, 589-596.	2.4	16
22	Fabrication and electrical characterization of Au/Pyronine-G/p-Si diode. Materials Science in Semiconductor Processing, 2014, 28, 20-25.	4.0	4
23	Growth and characterization of Ag/n-ZnO/p-Si/Al heterojunction diode by solâ€“gel spin technique. Journal of Alloys and Compounds, 2013, 550, 129-132.	5.5	69
24	Evaluation of Structural and Optical Properties of Mn-Doped ZnO Thin Films Synthesized by Sol-Gel Technique. Metallurgical and Materials Transactions A: Physical Metallurgy and Materials Science, 2012, 43, 5088-5095.	2.2	19
25	Structural and optical properties of ZnO thin films by the spin coating Sol-Gel method. Journal of Sol-Gel Science and Technology, 2011, 60, 66-70.	2.4	11
26	Capacitance and conductanceâ€“frequency characteristics of Auâ€“Sb/p-GaSe:Gd Schottky barrier diode. Vacuum, 2011, 85, 798-801.	3.5	26
27	Determination of Mass Attenuation Coefficients of Some Semiconductor and Biological Samples. Analytical Letters, 2010, 43, 1999-2008.	1.8	3
28	Electrical characterization of Ag/p-GaSe:Gd schottky barrier diodes. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 1958-1962.	2.7	12
29	Electrical characteristics and inhomogeneous barrier analysis of Auâ€“Be/p-InSe:Cd Schottky barrier diodes. Microelectronic Engineering, 2009, 86, 106-110.	2.4	10
30	Temperature variation of currentâ€“voltage characteristics of Au/Ni/n-GaN Schottky diodes. Physica E: Low-Dimensional Systems and Nanostructures, 2009, 41, 646-651.	2.7	53
31	Urbach tail and electric field influence on optical properties of InSe and InSe:Er single crystals. Applied Physics A: Materials Science and Processing, 2008, 90, 479-485.	2.3	11
32	The barrier-height inhomogeneity in identically prepared Ni/n-type 6H-SiC Schottky diodes. Applied Physics A: Materials Science and Processing, 2008, 91, 337-340.	2.3	26
33	The effects of the temperature and annealing on currentâ€“voltage characteristics of Ni/n-type 6Hâ€“SiC Schottky diode. Microelectronic Engineering, 2008, 85, 631-635.	2.4	31
34	Urbach tail and optical characterization of gadolinium-doped TlGaSe₂single crystals. Physica Scripta, 2008, 77, 025702.	2.5	19
35	Growth, Optical and Electirical Properties of In2S3, In1â^'xCdxS and CdS Thin Films by the (SILAR) Method. AIP Conference Proceedings, 2007, , .	0.4	1
36	Electric field influence on exciton absorption of Er doped and undoped InSe single crystals. Physica Scripta, 2007, 75, 424-430.	2.5	4

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37	Effective mass calculation for InSe, InSe:Er crystals. Physica E: Low-Dimensional Systems and Nanostructures, 2007, 36, 217-220.	2.7	11
38	Temperature-dependent optical absorption measurements and Schottky contact behavior in layered semiconductor n-type InSe(:Sn). Applied Surface Science, 2007, 253, 3899-3905.	6.1	44
39	Absorption measurement and Urbachâ€™s rule in InSe and InSe:Ho0.0025, InSe:Ho0.025 single crystals. Optical Materials, 2006, 28, 488-493.	3.6	18
40	Measurement of mass attenuation coefficients for holmium doped and undoped layered semiconductors InSe at different energies and the validity of mixture rule for crystals around the absorption edge. Journal of Quantitative Spectroscopy and Radiative Transfer, 2006, 102, 343-347.	2.3	16
41	Mass attenuation coefficients for n-type InSe, InSe:Gd, InSe:Ho and InSe:Er single crystals. Journal of Quantitative Spectroscopy and Radiative Transfer, 2005, 90, 399-407.	2.3	19
42	The Urbach tails and optical absorption in layered semiconductor TlGaSe2 and TlGaS2 single crystals. European Physical Journal D, 2005, 55, 93-103.	0.4	23
43	Urbach Tail and Optical Absorption in Layered Semiconductor TlGaSe2(1-x)S2xSingle Crystals. Physica Scripta, 2005, 72, 79-86.	2.5	19
44	Urbach Tail and Optical Investigations of Gd Doped and Undoped InSe Single Crystals. Physica Scripta, 2004, 70, 197-201.	2.5	9
45	Absorption Measurements in InSe:Ho Single Crystal Under an Electric Field. European Physical Journal D, 2004, 54, 377-385.	0.4	7
46	The Growth of P-type TlGaSe2(1-x)S2xSingle Crystals. European Physical Journal D, 2004, 54, 857-866.	0.4	3
47	Investigation of the electrical properties of Ho-doped InSe single crystal. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 85-90.	2.7	9
48	Electric field influence on absorption measurement in InSe single crystal. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 274-279.	2.7	20
49	The optical investigation of TlGa0.999Pr0.001Se2 and TlGaSe2 single crystals. Physica B: Condensed Matter, 2001, 293, 289-296.	2.7	17
50	Absorption Properties of Layer Semiconductor TlGaSe2 Doped Gd. Journal for Manufacturing Science and Production, 2001, 4, 113-120.	0.1	1
51	Growth and Temperature Dependence of Optical Properties of Er Doped and Undoped n-Type InSe. Japanese Journal of Applied Physics, 1999, 38, 5133-5136.	1.5	25
52	Growth and optical properties of Dy doped and undoped n-type InSe single crystal. Solid State Communications, 1999, 109, 665-669.	1.9	19
53	Growth and Optical Properties of Ho Doped n-Type Indium Selenide. Physica Status Solidi A, 1998, 168, 495-500.	1.7	17
54	Temperature dependence of galvanomagnetic properties for Gd doped and undoped p-type GaSe. Journal of Applied Physics, 1998, 83, 2030-2034.	2.5	16

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55	Electrothermal investigation of the switching effect in p-Type TlInSe2, TlInTe2, and TlGaTe2 chain chalcogenide semiconductors. Journal of Electronic Materials, 1996, 25, 1054-1059.	2.2	13